## **CLAIM AMENDMENTS**

1. (Currently Amended) A wet etching apparatus comprising:

a chemical-solution supply component for supplying a chemical solution on to be processed-on, the film being supported by a substrate, and

an ultraviolet-light radiating component for radiating irradiating the film with ultraviolet light to the film through the chemical solution.

- 2. (Currently Amended) The wet etching apparatus according to claim 1, wherein the ultraviolet-light radiating component radiates ultraviolet light having an energy higher than—a binding energy of constituent molecules of the film.
- 3. (Currently Amended) The wet etching apparatus according to claim 1, further comprising a drive unit for moving the ultraviolet-light radiating component, wherein the ultraviolet-light radiating component is moved at a location 2 mm to 5 mm above a surface of the film, when radiating of the film is being irradiated with the ultraviolet light.
- 4. (Currently Amended) The wet etching apparatus according to claim 1, wherein the ultraviolet-light radiating component comprises:
  - a light source generating the ultraviolet light; and
- a storage component for accommodating the light source and having a light-transmitting window for facing the film; and

wherein a nozzle in the chemical-solution supply component has a nozzle, disposed at a side of a gap between the light-transmitting window and the film, the nozzle for continuously supplying the chemical solution in the gap.

- 5. (Currently Amended) The wet etching apparatus according to claim 4, further comprising a stage for holding the substrate, wherein the stage including a pair of guides—are formed on the stage so as to be parallel to the nozzle—and sandwich, for sandwiching the substrate.
- 6. (Currently Amended) The wet etching apparatus according to claim 4, wherein including a layer of a surface-active agent is formed located at a surface of the light-transmitting window and contacting the chemical solution.

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7. (Currently Amended) The wet etching apparatus according to claim 4, wherein the chemical-solution supply component comprises:

a switching valve connected to the nozzle through a pipe and for switching between a supply of the chemical solution of and a supply of ultra-pure water;

a pipe for supplying the chemical solution and connected to the switching valve; and

a pipe for supplying the ultra-pure water and connected to the switching valve.

8. (Currently Amended) A method for wet etching of a film, comprising: supplying a chemical solution on to a film to be processed, the film being disposed on a substrate; and

radiating irradiating the film with ultraviolet light to the film through the chemical solution.

- 9. (Currently Amended) The method for wet etching according to claim 8, wherein including supplying—a the chemical solution and radiating irradiating the film with ultraviolet light are simultaneously—performed.
- 10. (Currently Amended) The method for wet etching according to claim 8, wherein the including irradiating the film with ultraviolet light having an energy higher than the binding energy of constituent molecules of the film-is radiated.
- 11. (Currently Amended) The method for wet etching according to claim 8, wherein the film is a high-k dielectric film performed an annealing treatment that has been annealed.